



## **IRFI520GPBF Information**



For Reference Only

Part Number IRFI520GPBF Manufacturer Vishay Siliconix

**Category** Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 100V 7.2A TO220FPPackageTO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **IRFI520GPBF Specifications**

Manufacturer Part Number Manufacturer Vishay Siliconix  Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 7.2A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Qperating Temperature  Mosperating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 7.2A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 360pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.3A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	IRFI520GPBF
Package         TO-220-3 Full Pack, Isolated Tab           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         7.2A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         16nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         360pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         37W (Tc)           Rds On (Max) @ Id, Vgs         270 mOhm @ 4.3A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab	Manufacturer	Vishay Siliconix
PackageTO-220-3 Full Pack, Isolated TabSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7.2A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs16nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)37W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.3A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         7.2A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         16nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         360pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         37W (Tc)           Rds On (Max) @ Id, Vgs         270 mOhm @ 4.3A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  100V  Current - Continuous Drain (Id) @ 25°C  7.2A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Supplier Device Package  Package / Case  N-Channel  MOSFET (Metal Oxide)  100V  7.2A (Tc)  7	Package	TO-220-3 Full Pack, Isolated Tab
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  7.2A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  100V  7.2A (Tc)  7.2A (Tc)  10V  4V @ 250μA  4V @ 20μA  4V @ 20	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7.2A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs16nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)37W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.3A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  For Voltage (Max) @ Vds  Through Hole  Supplier Device Package  TO-220-3 Full Pack, Isolated Tab	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs16nC @ 10VInput Capacitance (Ciss) (Max) @ Vds360pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)37W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.3A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  Package / Case  4V @ 250μA  16nC @ 10V  360pF @ 25V  +20V	Current - Continuous Drain (Id) @ 25°C	7.2A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  TO-220-3  Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  7	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)37W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.3A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	16nC @ 10V
FET Feature - Power Dissipation (Max) 37W (Tc) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.3A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	360pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  270 mOhm @ 4.3A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs270 mOhm @ 4.3A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	37W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	270 mOhm @ 4.3A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

#### **IRFI520GPBF Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# **IRFI520GPBF Payment Methods**



















## **IRFI520GPBF Shipping Methods**













If you have any question about IRFI520GPBF, please do not hesitate to contact us!

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